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Renesas Technology Corp. Customer Support Dept. April 1, 2003



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HSC276

Silicon Schottky Barrier Diode for Mixer



ADE-208-421A(Z)

Rev. 1 Dec. 1998

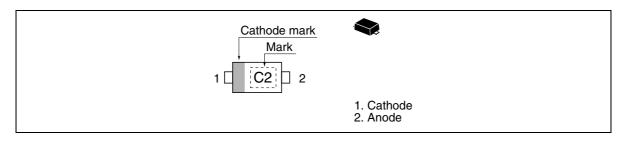
Features

- High forward current, Low capacitance.
- Ultra small Flat Package (UFP) is suitable for surface mount design.

Ordering Information

| Туре No. | Laser Mark | Package Code |
|----------|------------|--------------|
| HSC276 | C2 | UFP |

Pin Arrangement



HSC276

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Value | Unit |
|---------------------------|----------------|-------------|------|
| Reverse voltage | V _R | 3 | V |
| Average rectified current | I _o | 30 | mA |
| Junction temperature | Tj | 125 | ٥C |
| Storage temperature | Tstg | -55 to +125 | °C |

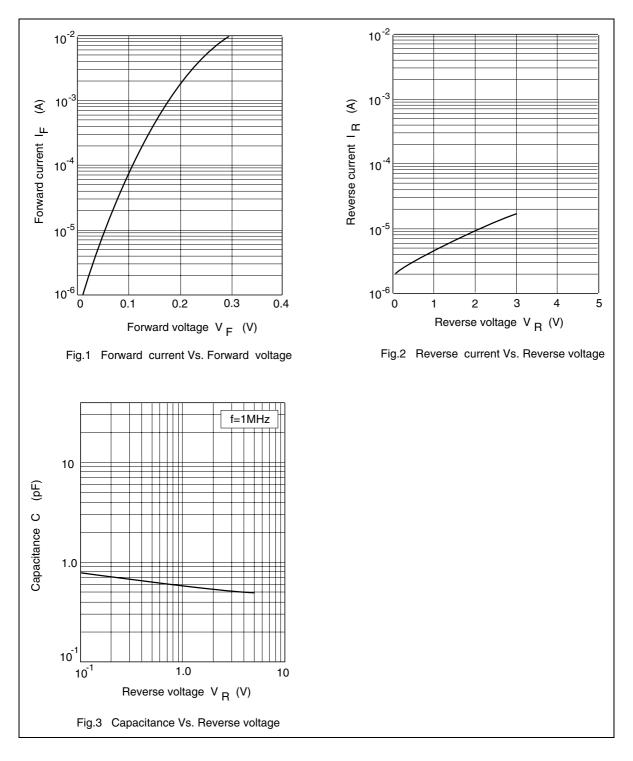
Electrical Characteristics

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Min | Тур | Max | Unit | Test Condition |
|------------------------------|----------------|-----|-----|------|------|---|
| Reverse voltage | V _R | 3 | _ | _ | V | I _R = 1 mA |
| Reverse current | I _R | | _ | 50 | μA | $V_{_{\mathrm{R}}} = 0.5 \mathrm{V}$ |
| Forward current | I _F | 35 | _ | _ | mA | $V_{F} = 0.5V$ |
| Capacitance | С | _ | _ | 0.85 | pF | V _R = 0.5V, f = 1 MHz |
| ESD-Capability ^{*1} | _ | 30 | | — | V | C=200pF , Both forward and reverse direction 1 pulse. |

Notes 1. Failure criterion ; $I_{_{\rm R}} \ge 100 \mu A$ at $V_{_{\rm R}} = 0.5 V$

Main Characteristic

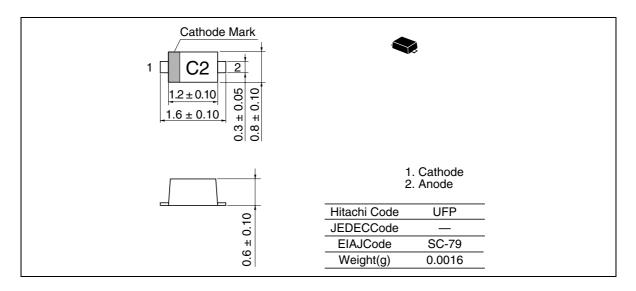


RENESAS

HSC276

Package Dimensions

Unit : mm





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